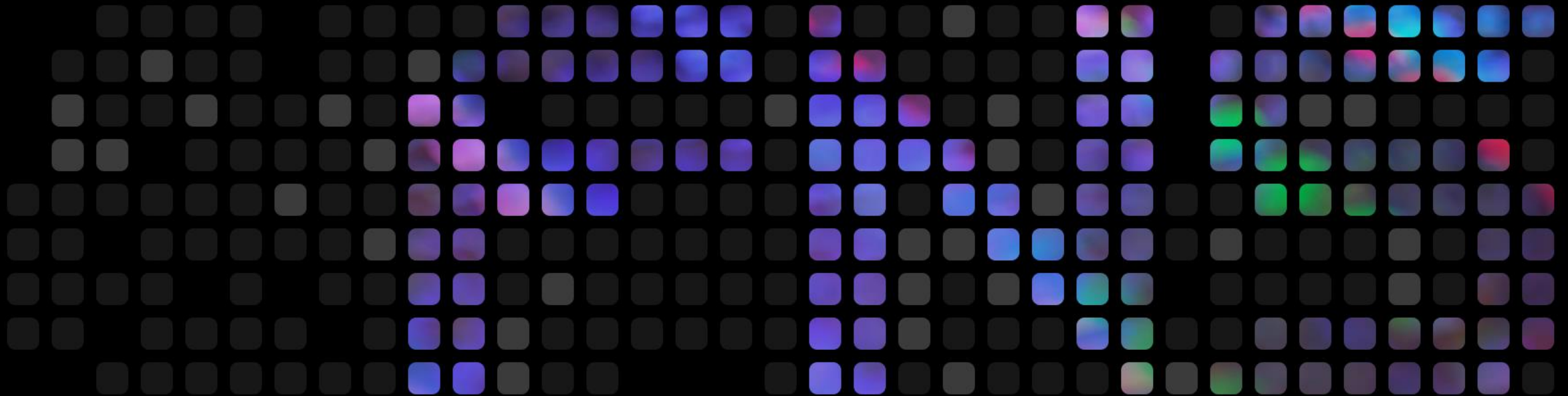


BEYOND LIMIT, BEYOND TECHNOLOGY





A Technology Specialist designing and manufacturing core semiconductor equipment technologies (RF, Plasma, ESC).

The only specialized company delivering integrated expertise
across manufacturing, development and repair of critical semiconductor components.

1. Company 03

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2. Core Competitiveness & Technology 15

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02. REMOTE PLASMA SOURCE 17

03. RF BLOCKING FILTER 20

04. RF MATCHER 23

05. RF GENERATOR 26

06. ESC SOLUTION 29



SECTION 1

Company

A Technology Specialist designing and manufacturing
core semiconductor equipment technologies (RF, Plasma, ESC).

01. Company Overview

- 1. Company Overview
- 2. Organization Chart
- 3. Revenue Status
- 4. Corporate History
- 5. Patents & Certifications
- 6. Business Sites
- 7. Global Network

02. R&D Infra

03. Future Strategy

- 1. Growth Performance
- 2. Sustainable Growth Strategy



01. Company
Overview

1. Company Overview

Challenging Beyond Limits, Powering the Core of Future Industries

FNS, Inc. is a leading technology specialist in plasma-based power and RF control solutions for semiconductor and display thin-film deposition and etching processes.

Leveraging advanced design and control capabilities across **Remote Plasma Source (RPS), RF Generators, RF Matchers, and DC Power Supplies**, we deliver optimized power transfer and stable plasma conditions that maximize process uniformity and repeatability

Our proprietary **DLC-based ESC coating technology, along with the localization of RF Blocking Filters and RPS**, enables highly durable and reliable process environments—driving both technological independence and performance excellence in critical semiconductor equipment.

*Beyond limits,
Beyond Technology*

OUR TECHNOLOGY CREATES
THE FUTURE FOR PEOPLE

MISSION

Driven by Technology

Achieved
USD **40** Million

NO.1 RF Solutions
Company

By 2027, we aim to reach USD 40 million in revenue through the advancement of Plasma and RF technologies and expansion into high-tech industries—establishing ourselves as leading RF solutions specialist.

VISION

Responsible Challenge

Mutual Respect

Excellence & Passion

CORE VALUE

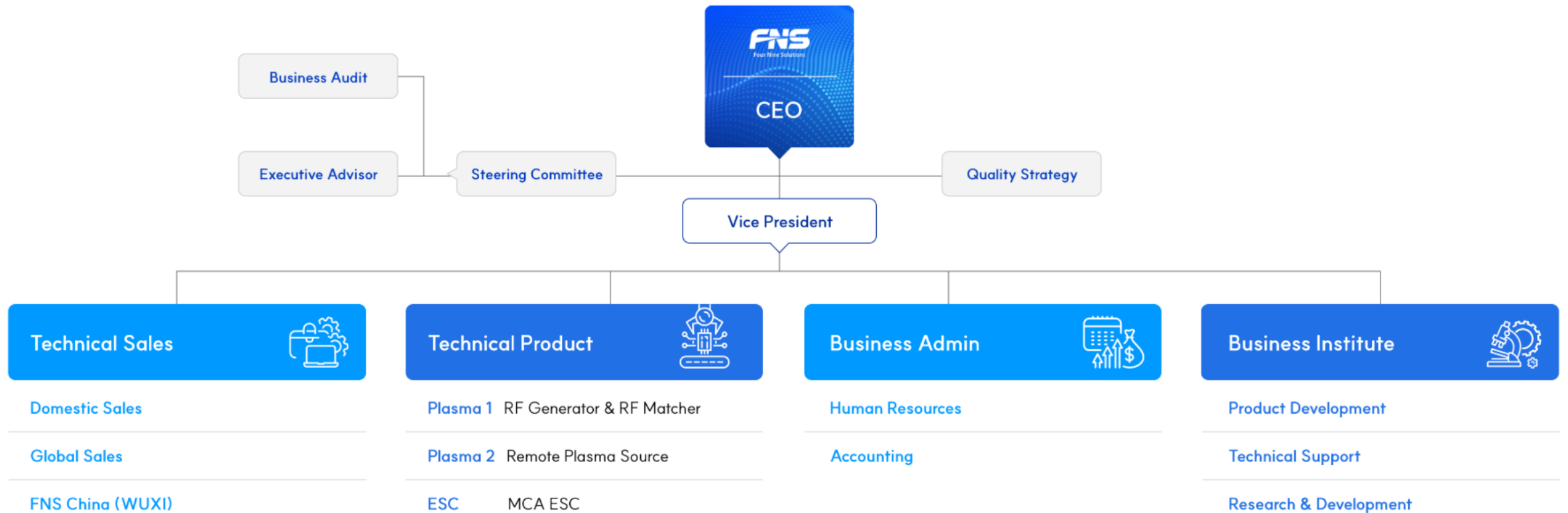


01. Company
Overview

2. Organization Chart

A technology-driven organization ensuring **process stability and quality reliability**

FNS, Inc. creates differentiated competitive advantage through a process-centric structure where R&D, manufacturing, and quality are seamlessly integrated





01. Company Overview

4. Corporate History

20 years built on deep process expertise—
an innovation journey proven by trust and performance

Since 2005 – 2015

The foundation of an RF solutions specialist

Building trust and
performance through
process-driven RF
technologies

2011 – 2015

- Establishment of R&D Center
- Registered Patent No. 10-1448148
- Registered Patent No. 10-1511240
- ISO 9001 Certified Quality Management System
- Approved Vendor for Samsung LED / SMD

2005 – 2010

- Tier-1 Supplier to SK Hynix Inc.
- Tier-1 Supplier to DB HiTek Co., Ltd.
- Tier-1 Supplier to LG Display Co., Ltd.
- Tier-1 Supplier to MagnaChip Semiconductor
- Launch of RPS Repair Services
- Launch of MCA ESC Repair Services
- Establishment of FNS Co., Ltd.



2016 – 2019

Establishing a robust technology framework
for sustainable growth

2019

- Establishment of Subsidiary in Wuxi, China
- Development and Qualification of RF Matcher Repair Technology

2018

- Certified as a Venture Company
- Establishment of Corporate R&D Center
- Implementation of RF Cable Manufacturing System
- Selection and Implementation of Smart Factory (MES)
- Certified as a Management Innovation SME (MAIN-BIZ)
- Certified as a Technology Innovation SME (INNO-BIZ)
- Recognized as a Family-Friendly Workplace by Gyeonggi Province

2017

- Relocation to New Headquarters

2016

- Tier-1 Supplier to Samsung Electronics Co., Ltd.
- ISO 14001 Environmental Management System Certification



2020 – Present

Earning global trust through proven performance

2022

- Certified as a Root Technology Company
- Designated as a Military Service Exemption Company
- Certified as a Specialized Company in Materials, Parts, and Equipment
- Launch of RF Blocking Filter "Quantum"

2021

- Certified as a Leading Company
- Recipient of the "USD 1 Million Export Tower" Award
- Selected as a Promising Export SME
- Development and Qualification of Revolution Repair Technology

2023 – Present

- Tier-1 Supplier to TSMC
- Tier-1 Supplier to Samsung C&T Corporation
- Official RF Filter Supplier to SEMES Co., Ltd.
- Tier-1 Supplier to Intel Corporation
- Gyeonggi Star Company
- Recognized as an Excellent Root Technology Workplace
- Promising SME by Gyeonggi Province
- Selected for SME Talent Development Program
- Recipient of the "USD 3 Million Export Tower" Award
- Gyeonggi Export Award
- Top 50 SME R&D
- Global Hidden Champion



01. Company Overview

5. Patents & Certifications

Trusted through global certifications and patents—**core assets redefining the future of semiconductor processes**

FNS, Inc. is a leading RF solutions specialist ensuring stability and reliability in semiconductor front-end processes through 99.99% precision quality control. With fully internalized core RF technologies, along with proven expertise, patents, and certifications, we drive innovation and establish strong global competitiveness in semiconductor process solutions.

Core Value

Three Core Values That Drive FNS



Ask yourself daily: "How much have I learned and grown as a professional today?"



Achieving our vision through limitless collaboration built on communication and mutual respect



- Recruit top talent and enable them to reach excellence
- A strong can-do mindset fuels deep engagement

Certificates & Awards





01. Company
Overview

6. Business Sites

RF solutions company building customer trust
through 99.99% quality control



China
Korea



Head Office (Yongin)

FNS, INC.

21, Tapsil-ro 58beon-gil, Giheung-gu,
Yongin-si, Gyeonggi-do, Republic of Korea

Established: Jan 2005



R&D Laboratory (Anyang)

142, LS-ro, Dongan-gu, Anyang-si,
Gyeonggi-do, Republic of Korea

Established: Mar 2023



FNS China (无锡艾普恩斯半导体技术有限公司)

无锡市新吴区菱湖大道228号天安智慧城2-208

Established: July 2019



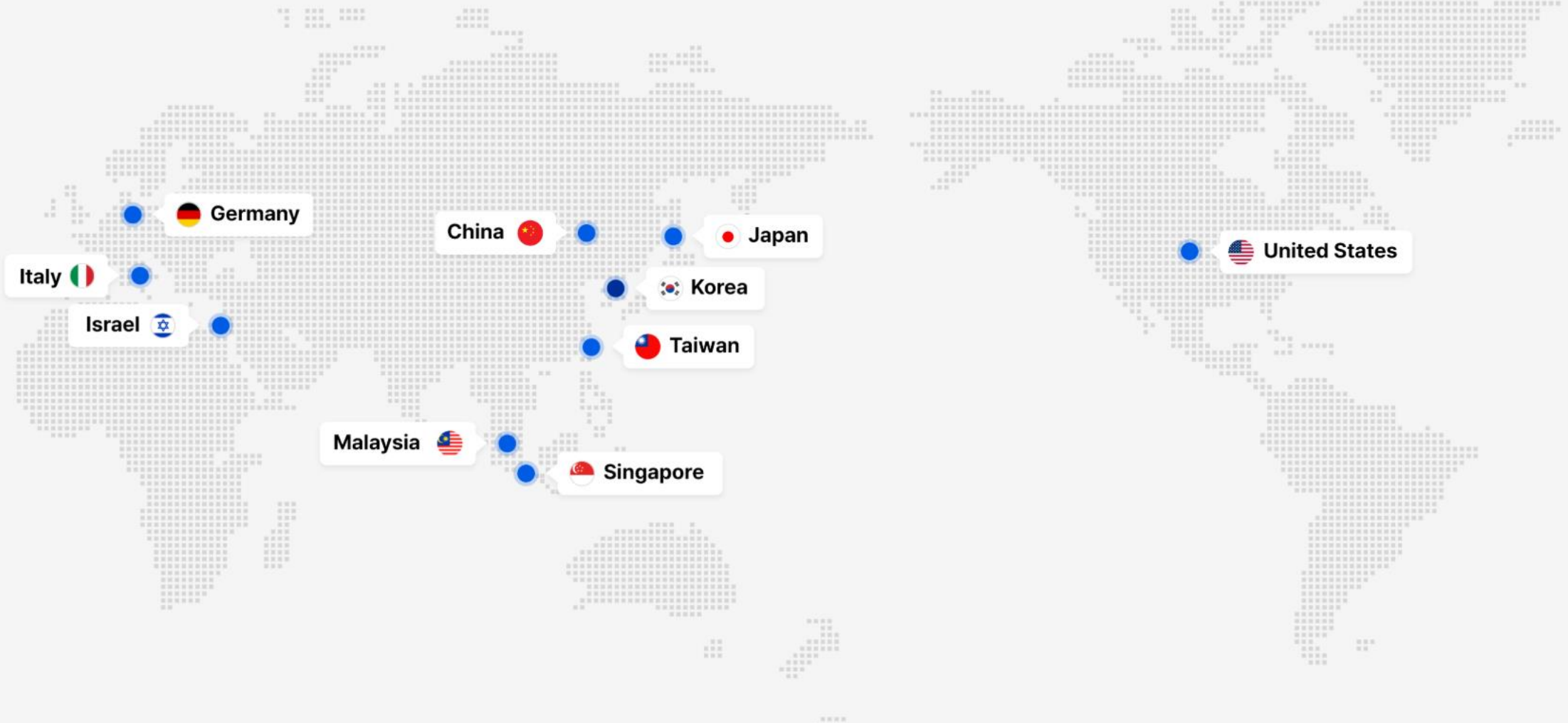
01. Company
Overview

7. Global Network

Proven technology validated across global fabs
—from leading domestic customers to worldwide markets

● Global Network

● Domestic Partners

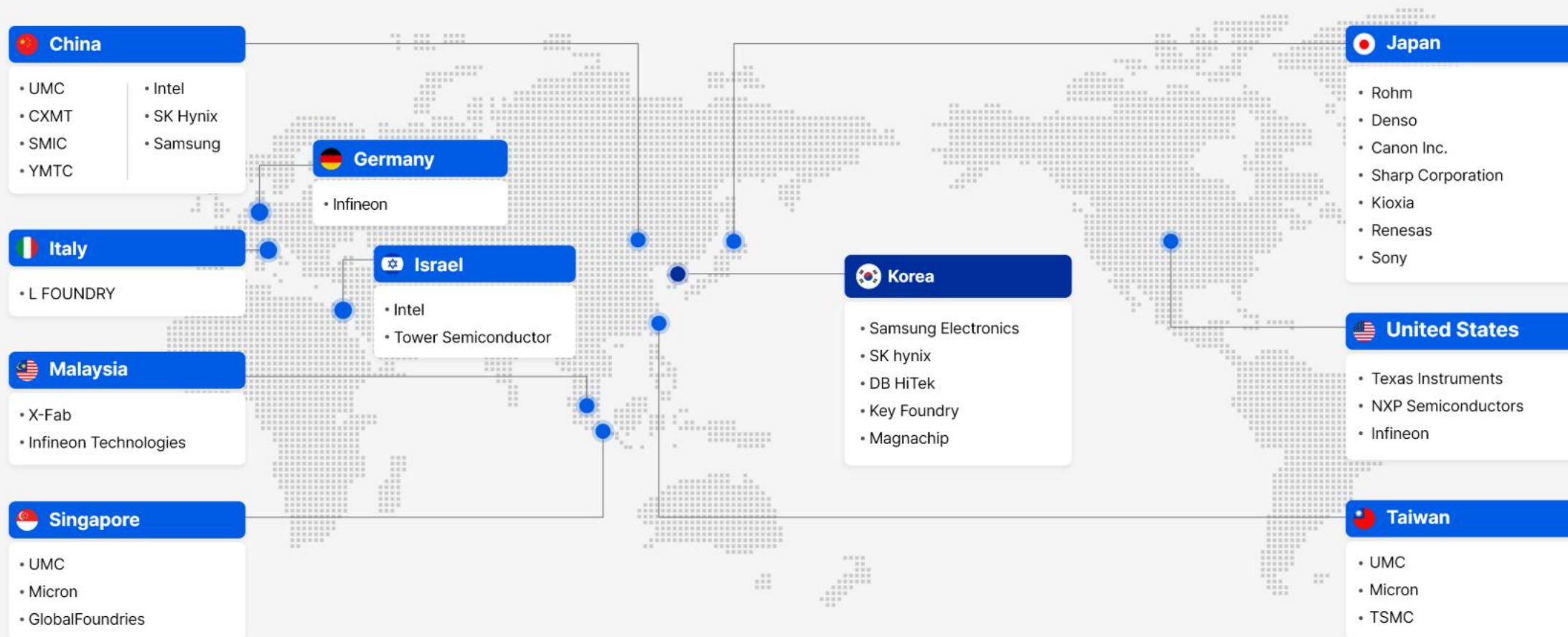




01. Company
Overview

7. Global Network

Proven technology validated across global fabs
—from leading domestic customers to worldwide markets





02. R&D Infra

1. R&D Infra

5% of revenue invested in R&D,
100% of growth driven by people

1. Proven Growth Performance Backed by Data

Total Revenue

* KRW 6.1 billion (2019) > KRW 17.8 billion (2024)

192% Growth

ESC Refurbishment Revenue

* Based on revenue from 2019 to 2024

300% Growth

Export Performance

* KRW 8.4 billion (2019) > KRW 54 billion (2024)

542% Growth

Recipient of the Export Tower Award

- * USD 1 Million Export Tower
- * USD 3 Million Export Tower



At FNS, we see people and their working environment as the core engines of growth.

Since undertaking national R&D projects, we have achieved rapid growth in both revenue and exports. Through sustained investment in R&D and talent development, we continue to strengthen our technological competitiveness. By creating an advanced research and manufacturing environment and a structured training system, we foster a culture where innovation is part of everyday work.

2. People-Centered R&D and Manufacturing Environment

Relocation to New
Headquarters in Yongin
(2017)

Redefining manufacturing with a modern and comfortable R&D and production environment **Bringing to life the belief that manufacturing can offer an exceptional workplace**

Building a
People-centered and
Inspiring Work Culture

Selected for SME
Talent Development
Program



Gyeonggi Star
Company



3. Sustainable Technology Innovation Framework



Ongoing investment of 5%
of annual revenue in R&D



Strong collaboration
between R&D and
Engineering teams



Structured training
programs conducted three
times per week,
combining theory with
practical application



Enhancing technical
expertise and problem-
solving capabilities through
hands-on, practice-driven
learning



03. Future Strategy

1. Growth Performance

Consistent Revenue Growth

Built on Solid Technological Strength

Over the past four years, FNS has maintained steady revenue growth driven by its core RF technologies. By delivering process-optimized solutions and expanding its global customer base, the company has built a stable and sustainable growth foundation.





03. Future Strategy

2. Sustainable Growth Strategy

A phased growth strategy connecting technological competitiveness to revenue and global expansion

Establishing a resilient revenue base through diversified income streams



- ✓ Strengthening profitability by expanding high value-added repair and maintenance services
- ✓ Ensuring recurring revenue through long-term service agreements with key customers
- ✓ Evolving from a product-focused model to an integrated service and manufacturing structure

Step1. Revenue Model Transformation

Broadening the growth base through strategic global market expansion



- ✓ Scaling revenue in key markets including Singapore, Taiwan, the U.S., Japan and etc.
- ✓ Capturing new opportunities in high-potential countries and customer segments
- ✓ Executing structured global expansion through tailored regional strategies and defined goals

Step2. Global Expansion Acceleration

Building sustainable competitive advantage through proprietary technology and manufacturing excellence



- ✓ Elevating global brand recognition through international exhibitions
- ✓ Expanding the product portfolio with a focus on the in-house developed Quantum series
- ✓ Accelerating next-generation innovation through increased R&D investment

Step3. Strengthening Core Technology Capabilities

Advancing as a leader in future semiconductor processes powered by unmatched technological expertise



SECTION 2

Technology

Core Competitiveness & Technology

02.

REMOTE PLASMA
SOURCE



03.

RF BLOCKING
FILTER



04.

RF
MATCHER



05.

RF
GENERATOR



06.

ESC
SOLUTION





01. Core Competencies

1. Core Competencies

Process optimization driven by technology design grounded in deep process expertise

Front-End Process

The stage of forming integrated circuits on a wafer

01. Wafer Preparation



02. Oxidation



03. Photolithography



04. Etching

Selective removal of materials

05. Thin Film Deposition

Deposition of dielectric and metal layers (CVD, PVD, ALD, etc.)

05. Interconnection

Electrical linking of circuit elements



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Point 01

Targeting the most challenging process segments

- ✓ Plasma stability is a key determinant of yield in fine linewidth and high aspect ratio structures
- ✓ RF and plasma control are essential to performance in etching, CVD, PVD, and interconnection processes
- ✓ FNS concentrates its technological expertise on high-complexity process segments to secure stability and repeatability



Point 03

Designing for the reproducibility and reliability demanded by equipment manufacturers



Point 02

Internalizing critical RF and Plasma components that define process performance



Point 04

Optimized RF tuning and power control aligned with customer-specific processes

01. Core Competencies

1. Core Competencies

Process optimization driven by technology design grounded in deep process expertise

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01. Core Competencies

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Process optimization driven by technology design grounded in deep process expertise

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The stage of forming integrated circuits on a wafer

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Electrical linking of circuit elements



Point 01

Targeting the most challenging process segments



Point 02

Internalizing critical RF and Plasma components that define process performance

Point 03

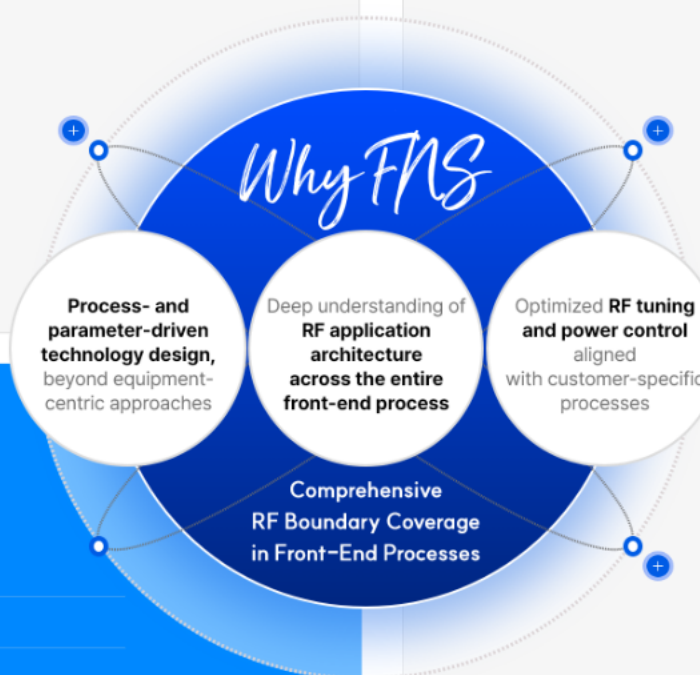
Designing for the reproducibility and reliability demanded by equipment manufacturers

- ✓ Securing stable power performance
- ✓ Ensuring uniform plasma distribution
- ✓ Optimizing process repeatability
- ✓ Designing for consistent operation under extended mass production conditions



Point 04

Optimized RF tuning and power control aligned with customer-specific processes



01. Core Competencies

1. Core Competencies

Process optimization driven by technology design grounded in deep process expertise

Front-End Process

The stage of forming integrated circuits on a wafer

01. Wafer Preparation



02. Oxidation



03. Photolithography



04. Etching

Selective removal of materials

05. Thin Film Deposition

Deposition of dielectric and metal layers (CVD, PVD, ALD, etc.)

05. Interconnection

Electrical linking of circuit elements





02. REMOTE PLASMA SOURCE

1. Technology Overview

FNS RPS – Plasma Supply Technology Engineered for Wafer Processes

What is RPS?

The Remote Plasma Source (RPS) generates plasma outside the process chamber and supplies only active radicals into the chamber.

Its key differentiator is that plasma is not generated directly inside the main chamber where the wafer resides, ensuring precise process control and enhanced yield.

Gas In > Plasma Generation > Radical Transport > Chamber Cleaning



Key Functions of RPS

Chamber Cleaning

- Efficient and stable dissociation of NF_3 , CF_4 , and O_2 gases into plasma
- Fluorine radicals effectively remove residues such as SiO_2 , SiN , and Poly through chemical reactions
- A critical post-process step for CVD, ALD, PVD, and etching operations

Minimized wafer damage

- Ion-free environment inside the chamber
- Reduced electrical and physical stress on the wafer
- Critical for advanced node and high-integration processes

Ensuring Process Stability

- Plasma generation confined within the RPS
- Maintaining stable thermal, pressure, and electrical conditions in the chamber
- Enhanced reproducibility across repeated process cycles

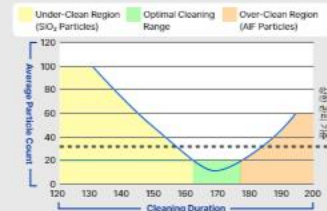
02. REMOTE PLASMA SOURCE

2. Differentiated Technology

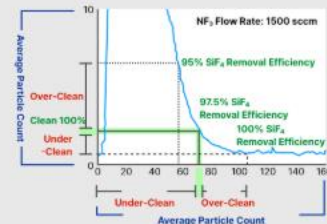
RPS goes beyond a simple cleaning source—delivering
a process-optimized plasma solution tailored to process conditions

Differentiated Technology

Particle Behavior as a Function of
Cleaning Time



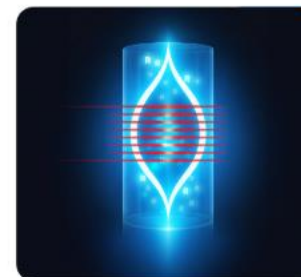
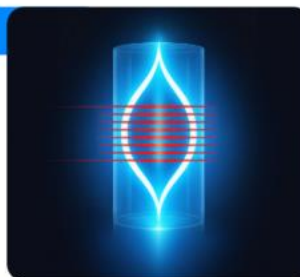
Cleaning Performance vs. Process Time



01. Plasma Technology

High-Density & Highly Stable Plasma Generation Technology

- Enables consistent and efficient dissociation of NF_3 , CF_4 , and O_2 through high-density, stable plasma generation
- Ensures stable plasma characteristics across the entire power spectrum, from low to high power



Radical Technology .02

Maximized Radical Generation & Minimized Loss

- Optimized radical generation with minimal loss during delivery
- Increased radical density at equivalent power for improved cleaning performance and stability

03. High-Durability Technology

Advanced Material & Thermal Management Design for High-Temperature Plasma Environments

- Engineered material selection and thermal architecture for stable operation in high-temperature plasma conditions
- Maintains plasma performance and system reliability under extended operating conditions



Process Optimization Technology .04

Customized Cleaning Optimization & Advanced Recipe Engineering

- Delivers process-specific cleaning solutions optimized for PVD, CVD, and Etch applications
- Leverages integrated control of gas, plasma, and time parameters to maximize process efficiency and stability

Process-Tailored Chamber Cleaning

Gas · Plasma · Time Optimization Expertise

Higher Efficiency, Extended Cleaning Cycles

03.

RF BLOCKING FILTER

FNS RF Blocking Filter is more than just a noise suppression component. It is a process reliability technology that ensures equipment stability and process reproducibility through precise RF interference control.

RF Environment Stabilization Technology

RF BLOCKING FILTER



03. RF
FILTER

1. Technology Overview

Stabilizing RF Environment Inside the Chamber

Quantum RF Filter

RF (Radio Frequency) Blocking Filter is a passive device that filters RF signals by allowing desired frequency bands to pass while blocking unwanted interference.

It maintains a stable RF environment inside the chamber by isolating interactions between equipment, ensuring process stability and reproducibility.

Application : PECVD + ALD + Etch (Dry / Wet) + Sputtering

Precision Plasma Environment Control for Reduced Process Variability

Minimized Plasma Fluctuation During Processing



Stable Chamber Conditions via Temperature & RF Control



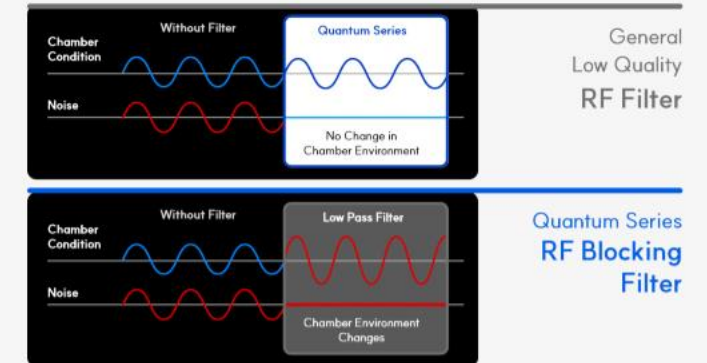
Customized RF Filtering by Frequency Range



Full Process Coverage RF Environment Solution



▼ Plasma Condition Variation with vs. without RF Filter



Why RF Blocking Filter Are Essential

Process Environment Evolution

Demand for Higher Yield in Advanced Node & Fine Pattern Technologies

Rapid Technology Shifts

High-Power, High-Temperature, High-Frequency Process Intensification

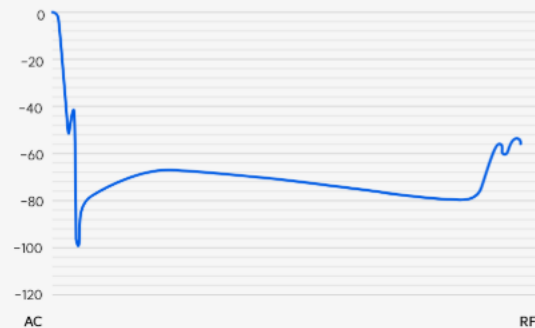
Critical Need for RF Filtering

Unstable Plasma & Quality Risks without RF Blocking Filters

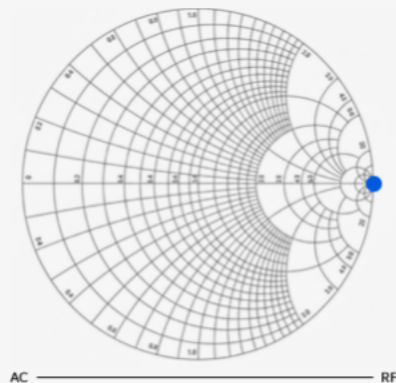
03. RF FILTER

Key Performance Indicators of RF Filters : High Rejection & High Impedance

HIGH REJECTION



HIGH IMPEDANCE



Specitication

Parameters	Frequency Range	40MHz & 13.56MHz
	40MHz Input Impedance [IZI mag]	Min. 1kΩ
	13.56MHz Input Impedance [IZI mag]	Min. 1kΩ
	Rejection at 40MHz [S21]	Max. -40 dB
	Rejection at 13.56MHz [S21]	Max. -40 dB
Power Rating	Rejection at 40MHz [S21]	Max. -40 dB
	Rejection at 13.56MHz [S21]	Max. -40 dB
Connector	Input [From Chamber]	SMPW-K-F Female
	Output [To Monitor]	SMPW-K-F Female
Physical	Input [From Chamber]	SMPW-K-F Female
	Output [To Monitor]	SMPW-K-F Female
Environmental & Cooling	Operating Temperature	+5 °C ~ +85 °C
	Cooling	Convection Cooling

×

Close

Precision Plasma for Reduced Pro

Minimized Plasma
Fluctuation
During Processing

Why RF Blocking Filter
Are Essential

Demand for Higher Yield in Advanced Node &
Fine Pattern Technologies

High-Power, High-Temperature,
High-Frequency Process Intensification

Unstable Plasma & Quality Risks
without RF Blocking Filters

nce.

Sputtering

out RF Filter

General
Low Quality
RF Filter

Quantum Series
RF Blocking
Filter

03. RF
FILTER

2. Differentiated Technology

Beyond Signal Conditioning — RF Filter as a Process RF Blocking Solution built on high-impedance and high-rejection design

Core Competency

All-In-One Filter : Integrated System

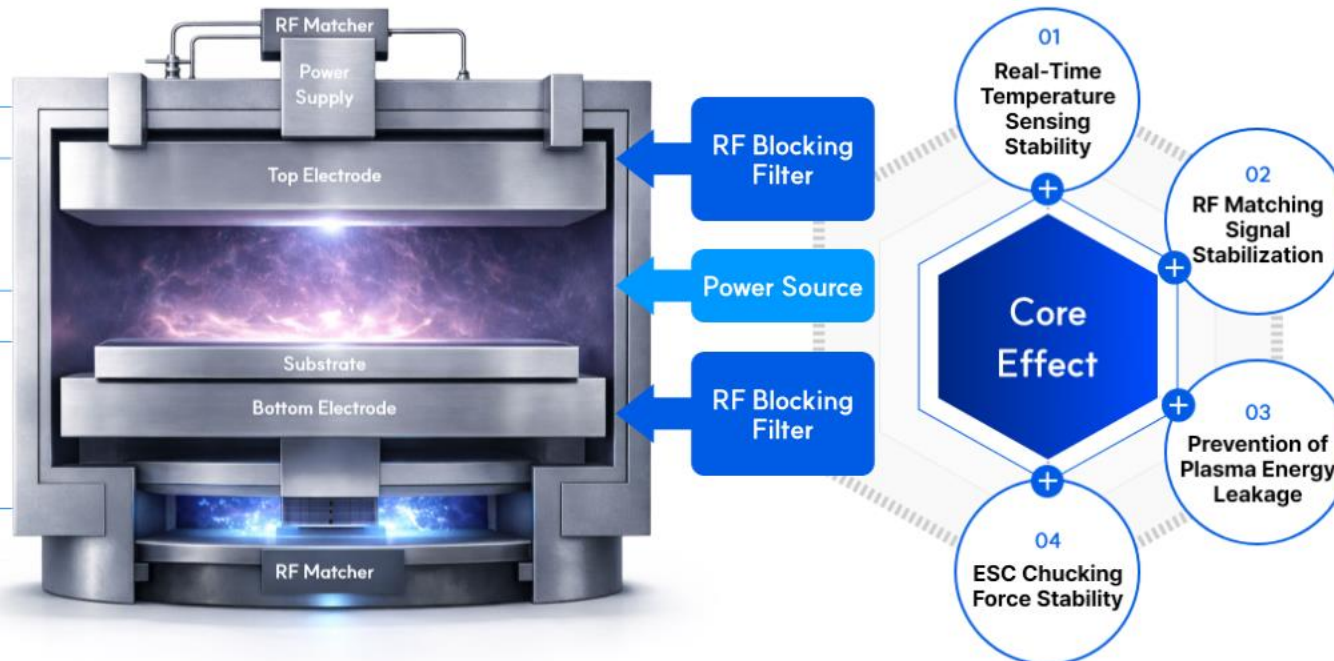
AC filter + DC filter + Power source
+ ESC Filter integrated into a unified system architecture

Customized Design

Precision Customization optimized for customer equipment specifications (voltage, frequency, temperature) and system architecture

High Impedance & Rejection Characteristics

High-impedance, high-resistance optimized multi-zone filters (1~18 zones)



04.

RF MATCHER

FNS RF Matcher is more than an impedance matching device.
It is a process stabilization technology that dynamically controls
RF power in real time, adapting to continuously changing plasma
conditions during processing.

Process-Driven RF Control Technology

RF MATCHER



04. RF
MATCHER

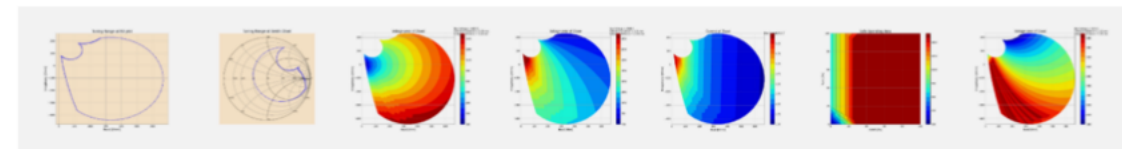
1. Technology Overview

Precision Energy Delivery Under Dynamic Plasma Conditions — FNS Matcher

What is FNS Matcher?

RF Matcher is not just a power delivery device. It is a core control technology that stabilizes the process by dynamically adjusting RF power in real time to match continuously changing plasma conditions.

FNS RF Matcher matches the impedance between the RF Generator and the chamber, minimizing power loss while precisely delivering the required power for optimal process performance.



Intelligent RF Matching Technology

- 01 Real-Time Impedance Matching Control
- +
- 02 Automated Control Based on Digital Matching Network
- +
- 03 Minimized Reflected Power
- +
- 04 Maximized Power Transfer Efficiency

Application Benefits

Consistent Plasma Quality

- Stable Plasma Density
- Enhanced Plasma Uniformity

Securing Process Reliability & Repeatability

- Stable RF Output Despite Process Variations
- Reliable Results in Long-Term Production

- Real-Time Impedance Tracking under Load Variations
- Auto Compensation for Gas, Pressure, and Plasma Changes
- Maintaining Optimal Matching for Process Stability
- Digital-Based Matching Network Architecture
- Fast Response for Stable Matching During Processing
- Stable RF Control Without Manual Intervention
- Suppressed Reflected Power from Impedance Mismatch
- Improved RF Generator Protection & System Reliability
- Reduced Forward Power Loss
- Accurate Energy Delivery to Plasma
- Maximized RF Energy Transfer Efficiency

04. RF
MATCHER

2. Differentiated Technology

Digital Impedance Matching Technology for Rapid Response to Process Variations

Based on an integrated power delivery design combining filter and matcher, it minimizes reflected power while ensuring plasma stability and process reproducibility.

Differentiated Technology

Improved Plasma Density & Uniformity

Enhanced
Process Reproducibility

Contributes to Equipment & RF Generator Protection

01. Integrated Power Delivery System

Filter + Matcher Unified Architecture

- Seamless integration of filter and matcher into a single power delivery system
- Lower harmonics and stable plasma with reduced flicker
- Enhanced bias stability for consistent process conditions

02. Fast Impedance Tracking & Auto Correction

Adaptive Precision Matching

- Real-time impedance tracking under dynamic load conditions
- Auto correction for gas, pressure, and plasma variations
- Optimized matching for minimized reflected power

03. Core Functions & Key Technologies

Precision-Driven Matching Performance

- Broad frequency coverage from 400 kHz to 60 MHz
- Supports power range from 100 W to 6.5 kW
- Auto-tuning via proprietary digital control system
- Stable and repeatable matching performance

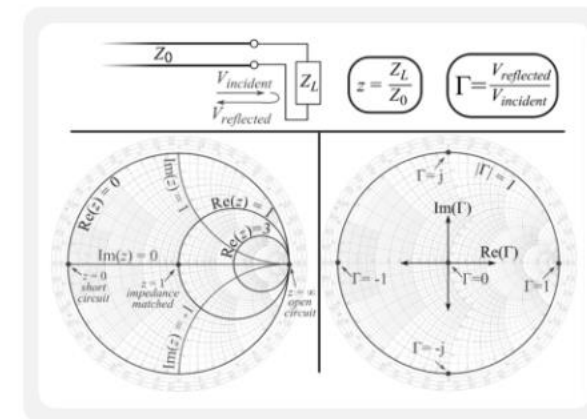
04. Reliability & Long-Term Stability

Engineered for Continuous Operation

- Robust design with integrated cooling system
- Consistent matching performance over extended runtime
- Validated through rigorous in-house testing and optimization

Performance Analysis Based on RF Impedance Theory
Validated extended matching range and stability in multi-frequency processes

Smith Chart & Reflection Coefficient Concept Diagram





05.

RF GENERATOR

A process-driven RF power source designed to ensure stable plasma generation and precise energy delivery for semiconductor and display manufacturing processes

KOR

ENG

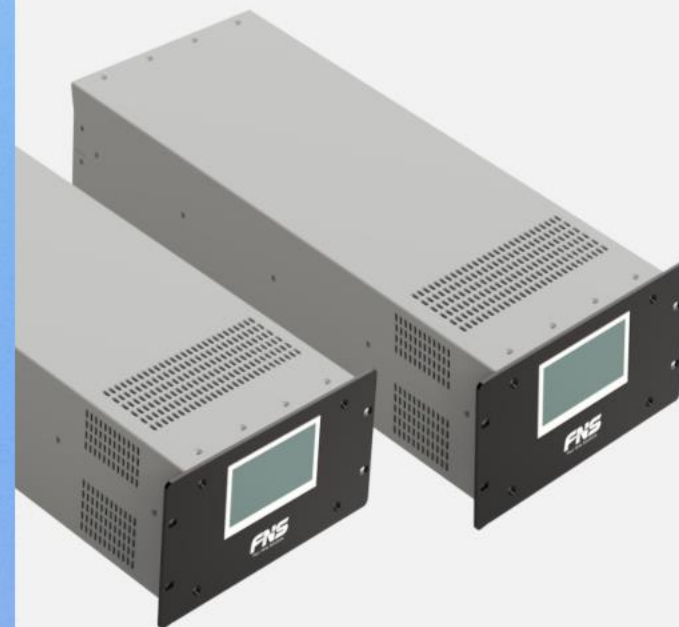


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Process-Driven RF Power Control Technology

RF GENERATOR





05. RF
GENERATOR

1. Technology Overview

Stable RF Output Regardless of Plasma Variations — FNS Generator

What is FNS Generator?

RF Generator converts AC power into high-frequency RF energy, enabling plasma generation in semiconductor and display manufacturing systems. It provides the necessary power to transform process gases into plasma within the chamber.

With a broad range of power and frequency options, FNS Generator delivers maximum efficiency through advanced control features optimized for diverse process conditions.

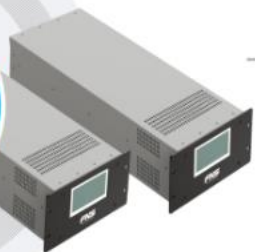
Key Feature

Stable RF Output under
Dynamic Plasma Loads

Power-Specific Custom
RF Generator Design

Reduced RF Fluctuation for
Output Stability

Core
Function



Output Stability Design

- Reliable RF output under high-power, high-frequency conditions
- Consistent and stable RF performance
- Reduced plasma variation between systems

Process-Adaptive Architecture

- Process-driven RF output stabilization design
- RF stabilization based on dynamic load variations
- Minimized RF output drift under gas, pressure, and plasma changes

Long-Term Reliability

- Thermally Stable for Long-Run Processes
- Engineered for Consistent RF Output

Process
Benefits Stable
RF Output

01

Higher RF Power
Transfer Efficiency

02

Reduced
Plasma Instability

03

Reliable for
Long-Term
Production

05. RF
GENERATOR

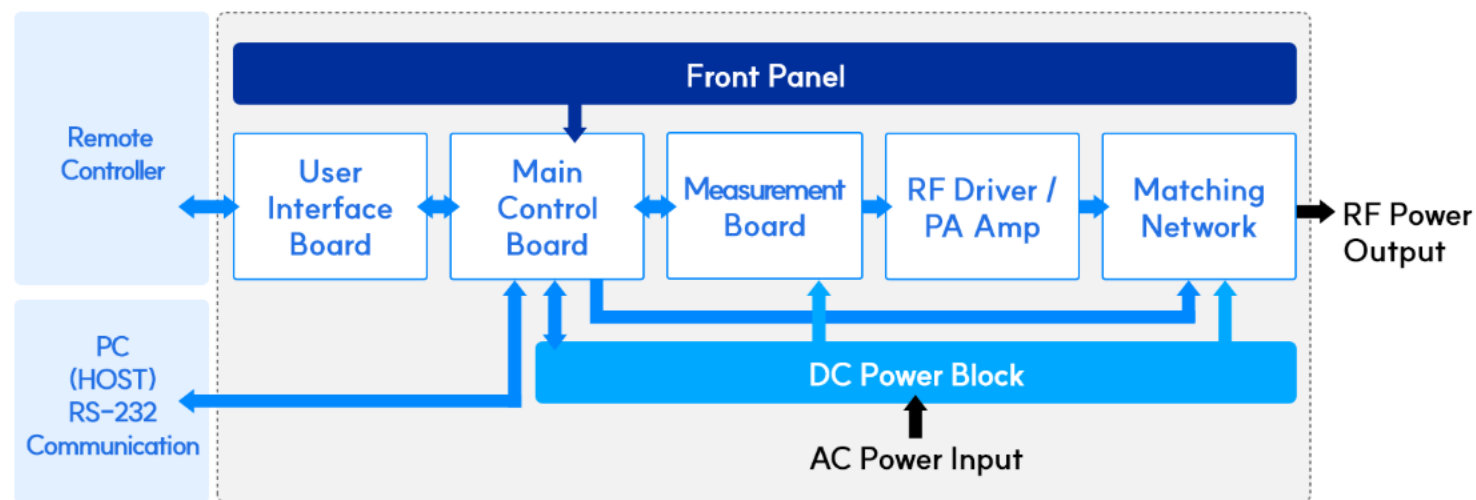
2. Differentiated Technology

Engineered RF Generator for consistent,
stable output under dynamic process loads and changing environments

FNS
RF GENERATOR
Specification

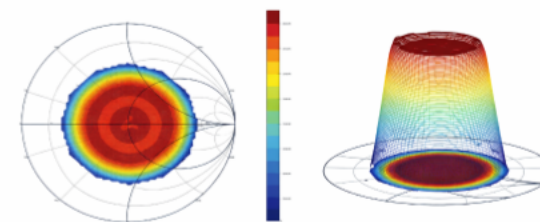


RF Output Stabilization Architecture of Generator System

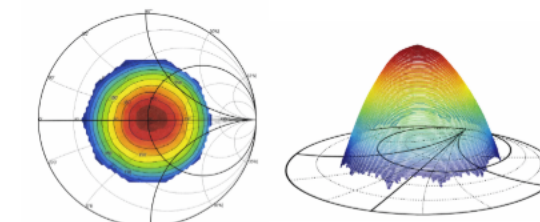


Stability of RF Output Distribution

Equivalent Power Profile



<dP/dZ Power Profile @ VSWR 1.2 to 4>





05. RF
GENERATOR

RF Output Stab

Remote
Controller



PC
(HOST)
RS-232
Communication



Specification

Frequency	400 kHz / 2 MHz / 13.56 MHz / 27.12 MHz / 40.68 MHz / 60 MHz
Power	100 W ~ 8 kW
Power Accuracy	± 1%
Power Step	Standard - 1W, Option - 0.1W / 5W / 10W (Customize)
RF Output Connector	Standard(Female). N ≤ 1kW / HN ≤ 3kW / DIN ≤ 5kW
Out Impedance	50Ω
Harmonics & Spurious	≤ -50 dBc
Efficiency	≥ 55%
Cooling Method	Air Cooling / Water Cooling
Input V, Frequency	200 ~ 240 VAC 1Ø / 3Ø, 47Hz ~ 63Hz
Protection Functions	Standard - Over Temperature(≥ 70°C) / Safety Interlock, Option - V/I Impedance
Operating Temperature	5 ~ 40 °C
Dimension&Weight	Customized
Interface	Analog User Port, RS-232C, Option - CEX

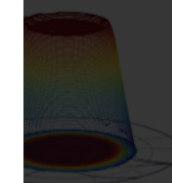
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Close

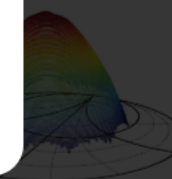
FNS
RF GENERATOR
Specification



tribution



to 4>



06.

ESC SOLUTION

FNS RF Matcher is more than an impedance matching device.
It is a process stabilization technology that dynamically controls
RF power in real time, adapting to continuously changing plasma
conditions during processing.

Minimized Contact,
Maximum Process Protection

MCA ESC



06. ESC
SOLUTION

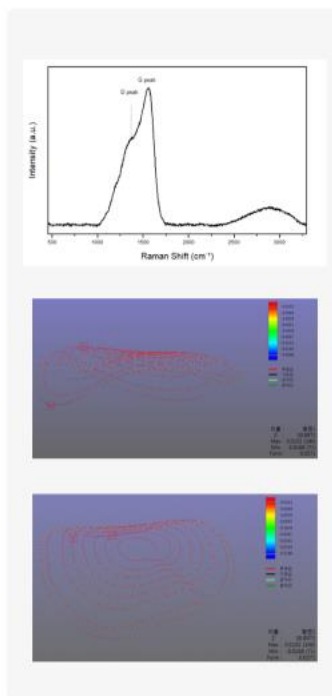
1. Technology Overview

FNS MCA ESC Total Solution

What is MCA ESC?

MCA ESC(Minimum Contact Area Electrostatic Chuck)minimizes wafer-to-chuck contact through advanced electrostatic design.

By applying failure-mode-based overhaul solutions, it enhances ESC performance while securing process quality and wafer stability in advanced node and high-integration environments.



Advanced
Deposition
Capabilities

Chucking Film

Heater Film

Chucking Line

Heater Line

Inner
Outer

01

High
Hardness

+

02

Low Friction
Coefficient

+

03

High Strength,
& Heat Resistance

+

04

Superior
Wear Resistance

A Zone

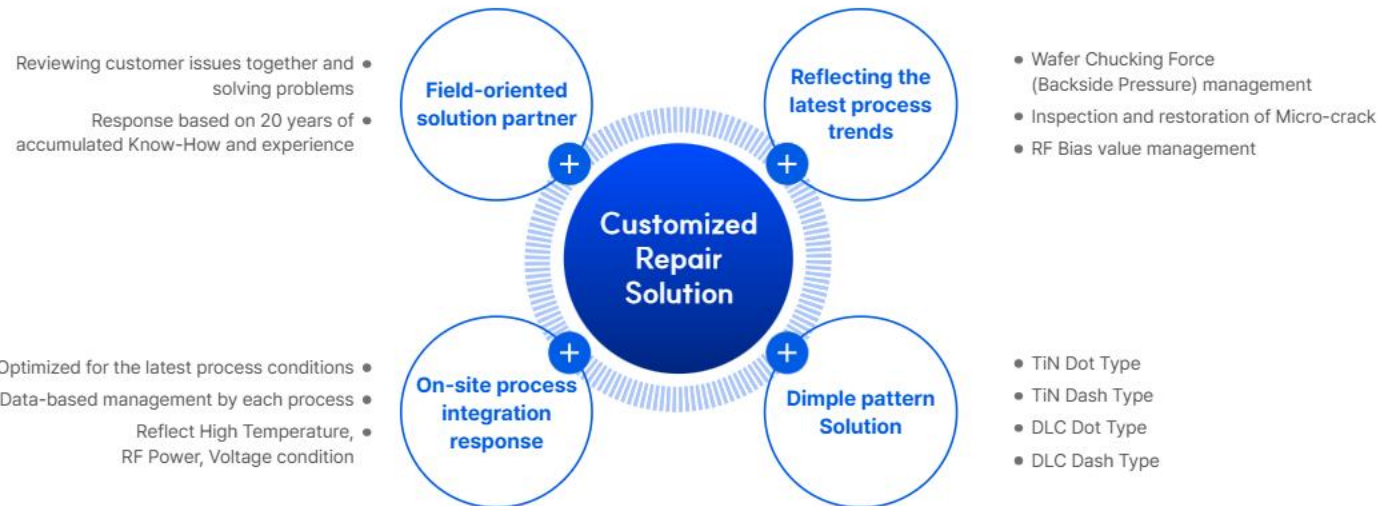
B Zone

C Zone

06. ESC
SOLUTION

2. Differentiated Technology

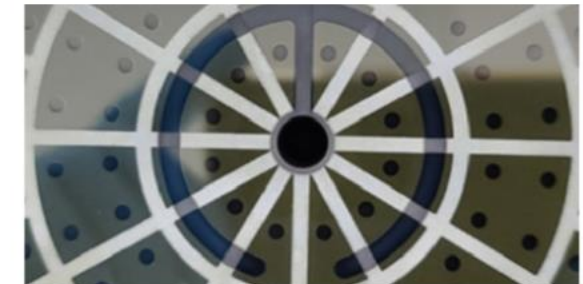
Through DLC, TiN deposition technology and field data-based analysis, **Achieving optimal repair results matching equipment conditions**



Solution Records

- | | | | | |
|-------------------|--------------------------|-----------|---------------|--------------------------|
| • Chucking force | • Temperature | • Edge | • Micro-crack | • Particle / FDC |
| • Center-Tap Bias | • Insulation Resistivity | • Mapping | • Bellows | • Cooling line / TC wire |
| • Surface Voltage | • Wafer | • RF Bias | • Wire | |

Technical Strength



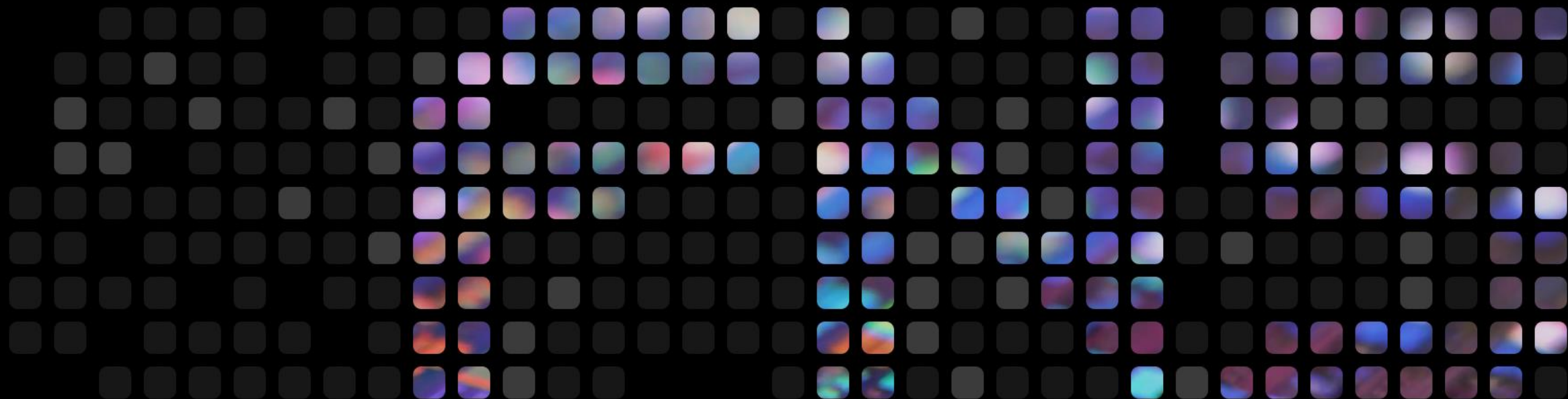
DLC Solution

- High electrical insulation properties
- Stable application even in strong RF environments
- Maintains durability even under high-output conditions
- Ensures excellent wear resistance



TiN Solution

- Low electrical insulation properties
- Suitable for high-temperature process conditions
- Applicable to environments requiring structural stability and thermal responsiveness



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